

Integrated Device Technology, Inc.

HIGH-SPEED BiCMOS 10-BIT INTERFACE LATCHES

ADVANCE INFORMATION
IDT54/74FBT841A
IDT54/74FBT841B
IDT54/74FBT841C

FEATURES:

- Functionally equivalent to the 54/74BCT841 series
- **IDT54/74FBT841B 20% faster than the 841A**
- **IDT54/74FBT841C 15% faster than the 841B**
- Significant reduction in ground bounce from standard CMOS devices
- TTL compatible input and output levels
- Low power in all three states
- $\pm 10\%$ power supply for both military and commercial grades
- JEDEC standard pinout for DIP, SOIC and LCC packages
- Military product compliant to MIL-STD-883, Class B

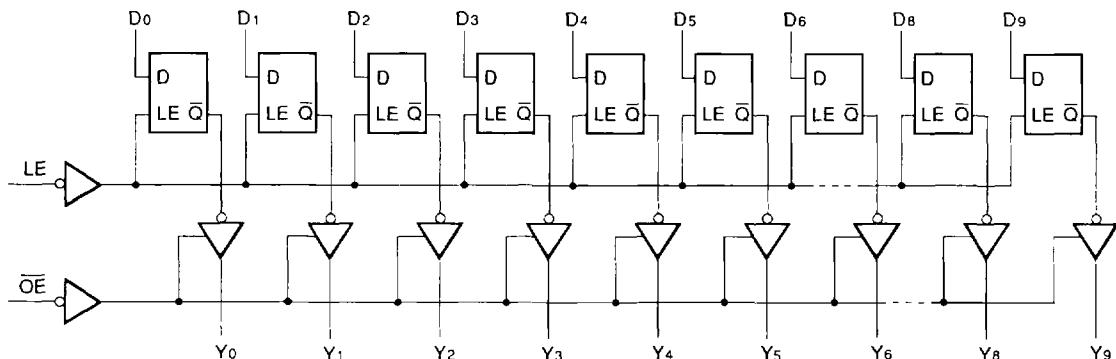
DESCRIPTION:

The FBT series of BiCMOS Bus Interface Latches are built using advanced BiCEMOS™, a dual metal BiCMOS technology. This technology is designed to supply the highest device speeds while maintaining CMOS power levels.

The IDT54/74FBT841 series are 3-state, 10-bit bus interface latches.

The FBT series of bus interface devices are ideal for use in designs needing to drive large capacitive loads with low static(DC) current loading. All data inputs have a 200mV typical input hysteresis for improved noise rejection.

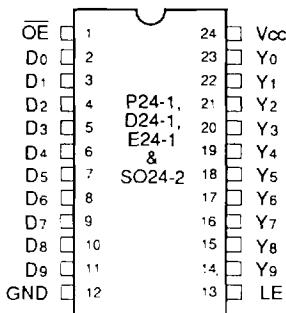
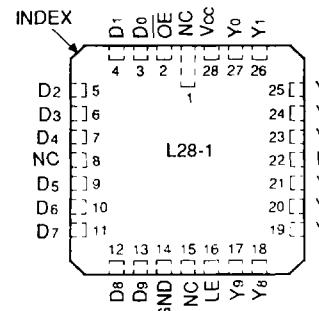
FUNCTIONAL BLOCK DIAGRAM



6

2600 drw C1

PIN CONFIGURATIONS

DIP/SOIC/CERPACK
TOP VIEWLCC
TOP VIEW

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MILITARY AND COMMERCIAL TEMPERATURE RANGES

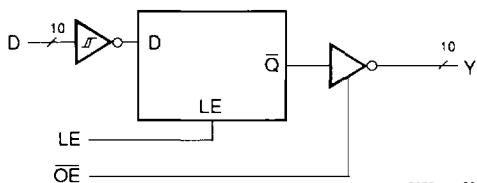
APRIL 1990

PIN DESCRIPTION

Name	I/O	Description
D ₀₋₉	I	The latch data inputs.
LE	I	The latch enable input. The latches are transparent when LE is HIGH. Input data is latched on the HIGH-to-LOW transition.
Y ₀₋₉	O	The 3-state latch outputs.
OE	I	The output enable control. When OE is LOW, the outputs are enabled. When OE is high, the outputs Y _i are in the high-impedance (off) state.

2600 tbl 05

LOGIC SYMBOL



2600 drw 03

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	0.5	0.5	W
IOUT	DC Output Current	120	120	mA

NOTES:

2600tbl 01

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.

FUNCTION TABLE⁽¹⁾

Inputs			Internal	Outputs	
OE	LE	Di	Qi	Y _i	Function
H	X	X	X	Z	High Z
H	H	L	L	Z	High Z
H	H	H	H	Z	High Z
H	L	X	NC	Z	Latched (High Z)
L	H	L	L	L	Transparent
L	H	H	H	H	Transparent
L	L	X	NC	NC	Latched

NOTE:

1 H = HIGH, L = LOW, X = Don't Care, NC = No Change, Z = High Impedance

2600tbl 06

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	8	pF

NOTE:

2600tbl 02

- This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Commercial: TA = 0°C to +70°C, V_{CC} = 5.0V ± 10%; Military: TA = -55°C to +125°C, V_{CC} = 5.0V ± 10%

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V _{IH}	Input HIGH Level	Guaranteed Logic HIGH Level		2.0	—	—	V
V _{IL}	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I _{IH}	Input HIGH Current	V _{CC} = Max., V _I = 2.7V		—	—	10	μA
I _{IL}	Input LOW Current	V _{CC} = Max., V _I = 0.5V		—	—	-10	μA
I _{OZH}	High Impedance	V _{CC} = Max.	V _O = 2.7V	—	—	50	μA
I _{OZL}	Output Current		V _O = 0.5V	—	—	-50	μA
I _I	Input HIGH Current	V _{CC} = Max., V _I = 5.5V		—	—	100	μA
V _{IK}	Clamp Diode Voltage	V _{CC} = Min., I _N = -18mA		—	-0.7	-1.2	V
I _{OS}	Short Circuit Current	V _{CC} = Max., V _O = GND ⁽³⁾		-75	-150	-225	mA
V _{OH}	Output HIGH Voltage	V _{CC} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OH} = -12mA MIL. I _{OH} = -15mA COM'L.	2.4	3.3	—	V
			I _{OH} = -18mA MIL. I _{OH} = -24mA COM'L.	2.0	3.0	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 32mA MIL. I _{OL} = 48mA COM'L.		—	0.3	0.5	V
V _H	Input Hysteresis	V _{CC} = 5V		—	200	—	mV
I _{OFF}	Bus Leakage Current	V _{CC} = 0V, V _O = 4.5V		—	—	100	μA
I _{CC}	Quiescent Power Supply Current	V _{CC} = Max. V _{IN} = GND or V _{CC}		—	0.2	1.5	mA

NOTES:

2600 to 03

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at V_{CC} = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
ΔI_{CC}	Quiescent Power Supply Current (Inputs TTL HIGH)	V _{CC} = Max. V _{IN} = 3.4V ⁽³⁾		—	—	2.0	mA
I _{CCD}	Dynamic Power Supply Current ⁽⁴⁾	V _{CC} = Max., Outputs Open \bar{OE} = GND One Input Toggling LE = V _{CC} 50% Duty Cycle	V _{IN} = V _{CC} V _{IN} = GND	—	—	0.25	mA/ MHz
I _C	Total Power Supply Current ⁽⁶⁾	V _{CC} = Max., Outputs Open f_i = 10MHz, 50% Duty Cycle \bar{OE} = GND, LE = V _{CC} One Bit Toggling	V _{IN} = V _{CC} V _{IN} = GND	—	—	4.0	mA
		V _{CC} = Max., Outputs Open f_i = 2.5MHz, 50% Duty Cycle \bar{OE} = GND, LE = V _{CC} Ten Bit Toggling	V _{IN} = 3.4V V _{IN} = GND	—	—	5.0	
		V _{CC} = Max., Outputs Open f_i = 2.5MHz, 50% Duty Cycle \bar{OE} = GND, LE = V _{CC} Ten Bit Toggling	V _{IN} = V _{CC} V _{IN} = GND	—	—	7.8 ⁽⁵⁾	
		V _{CC} = Max., Outputs Open f_i = 2.5MHz, 50% Duty Cycle \bar{OE} = GND, LE = V _{CC} Ten Bit Toggling	V _{IN} = 3.4V V _{IN} = GND	—	—	17.8 ⁽⁵⁾	

NOTES:

2600 tbt 04

1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type

2. Typical values are at V_{CC} = 5.0V, +25°C ambient, and maximum loading.

3. Per TTL driven input (V_{IN} = 3.4V); all other inputs at V_{CC} or GND

4. This parameter is not directly testable, but is derived for use in Total Power Supply calculations

5. Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.

6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$I_C = I_{CC} + \Delta I_{CCD} \cdot N_T + I_{CCD}(f_{CP}/2 + fN_I)$

I_{CC} = Quiescent Current

ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)

D_H = Duty Cycle for TTL Inputs High

N_T = Number of TTL Inputs at D_H

I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

f_i = Input Frequency

N_I = Number of Inputs at f_i

All currents are in millamps and all frequencies are in megahertz

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Condition ⁽¹⁾	54/74FBT841A				54/74FBT841B				54/74FBT841C				Unit	
			Com'l.		Mil.		Com'l.		Mil.		Com'l.		Mil.			
			Min. ⁽²⁾	Max.												
tPLH tPHL	Data (Di) to Output (Yi) (LE = HIGH)	CL = 50pF RL = 500Ω	—	8.0	—	—	—	6.5	—	—	—	5.5	—	—	ns	
tPLH tPHL		CL = 300pF ⁽³⁾ RL = 500Ω	—	—	—	—	—	—	—	—	—	—	—	—	ns	
tSU	Data to LE Set-up Time	CL = 50pF	—	1.5	—	—	—	1.5	—	—	—	1.5	—	—	ns	
tH	Data to LE Hold Time	RL = 500Ω	—	3.5	—	—	—	2.5	—	—	—	2.5	—	—	ns	
tPLH tPHL	Latch Enable (LE) to Yi	CL = 50pF RL = 500Ω	—	10.0	—	—	—	8.0	—	—	—	6.4	—	—	ns	
tPLH tPHL		CL = 300pF ⁽³⁾ RL = 500Ω	—	—	—	—	—	—	—	—	—	—	—	—	ns	
tw	LE Pulse Width HIGH	CL = 50pF RL = 500Ω	—	4.0	—	—	—	4.0	—	—	—	4.0	—	—	ns	
tPZH tPZL	Output Enable Time OE to Yi	CL = 50pF RL = 500Ω	—	8.0	—	—	—	8.0	—	—	—	6.5	—	—	ns	
tPZH tPZL		CL = 300pF ⁽³⁾ RL = 500Ω	—	—	—	—	—	—	—	—	—	—	—	—	ns	
tPHZ tPLZ	Output Disable Time OE to Yi	CL = 50pF ⁽³⁾ RL = 500Ω	—	15.0	—	—	—	7.0	—	—	—	6.0	—	—	ns	
tPHZ tPLZ		CL = 50pF RL = 500Ω	—	—	—	—	—	—	—	—	—	—	—	—	ns	

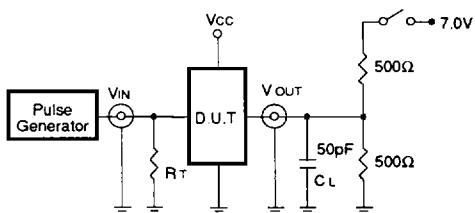
NOTES:

1. See test circuits and waveforms
 2. Minimum limits are guaranteed but not tested on Propagation Delays
 3. This parameter guaranteed but not tested.

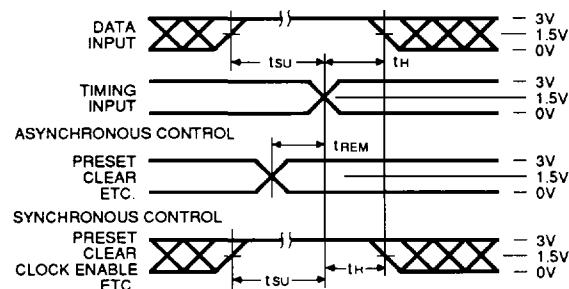
2600 tdi 07

TEST CIRCUITS AND WAVEFORMS

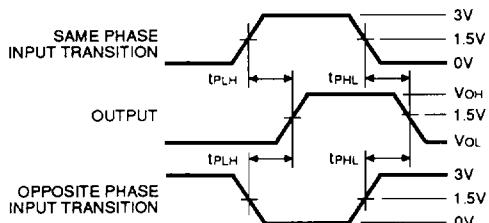
TEST CIRCUITS FOR ALL OUTPUTS



SET-UP, HOLD AND RELEASE TIMES



PROPAGATION DELAY



SWITCH POSITION

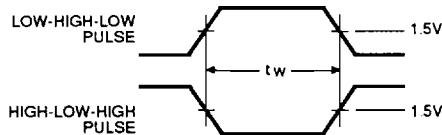
Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Outputs	Open

DEFINITIONS:

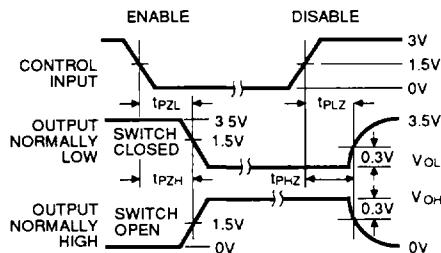
CL = Load capacitance; includes jig and probe capacitance.
RT = Termination resistance; should be equal to Zout of the Pulse Generator.

2600 tb 08

PULSE WIDTH



ENABLE AND DISABLE TIMES



NOTES

2600 drw 04

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate ≤ 1.0 MHz; $Z_0 \leq 50\Omega$; $t_f \leq 2.5$ ns; $t_R \leq 2.5$ ns.

ORDERING INFORMATION

IDT	XX	FBT	XXXX	X	X		
Temperature Range		Device Type		Package		Process	
						Blank	Commercial MIL-STD-883, Class B
						P	Plastic DIP
						D	CERDIP
						SO	Small Outline IC
						L	Leadless Chip Carrier
						E	CERPACK
					841A		Non-inverting 10-Bit Bus Interface Latch
					841B		High-Speed Non-inverting 10-Bit Bus Interface Latch
					841C		Very High-Speed Non-inverting 10-Bit Bus Interface Latch
					54		-55°C to +125°C
					74		0° to +70°C

2600 dw 04